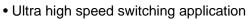
# SILICON EPITAXIAL PLANAR DIODE

## Features

- Small package
- · Low forward voltage
- Fast reverse recovery time
- Small total capacitance

#### **Applications**



### Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V <sub>RM</sub>	85	V
Reverse Voltage	V <sub>R</sub>	80	V
Average Forward Current	Ι <sub>ο</sub>	100	mA
Maximum Peak Forward Current	I <sub>FM</sub>	300	mA
Surge Current (10 ms)	I <sub>FSM</sub>	2	А
Power Dissipation	P <sub>tot</sub>	150	mW
Junction Temperature	Tj	150	°C
Storage Temperature Range	T <sub>s</sub>	- 55 to + 150	°C

#### Characteristics at T<sub>a</sub> = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I <sub>F</sub> = 100 mA	V <sub>F</sub>	1.2	V
Reverse Current at $V_R = 30 V$ at $V_R = 80 V$	I <sub>R</sub>	0.1 0.5	μΑ
Total Capacitance at $V_R = 0$ , f = 1 MHz	C <sub>T</sub>	4	pF
Reverse Recovery Time at I <sub>F</sub> = 10 mA	t <sub>rr</sub>	4	ns



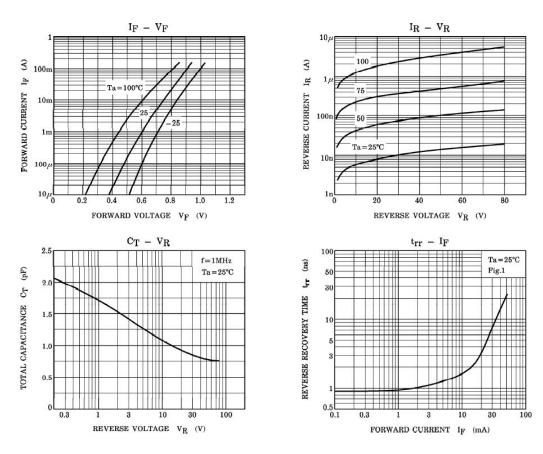
SEMTECH ELECTRONICS LTD. (Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)

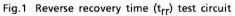


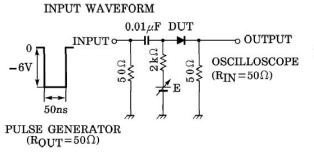
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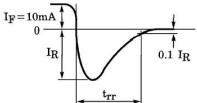
Marking Code: A1 SOT-23 Plastic Package







#### OUTPUT WAVEFORM









Dated : 10/10/2008